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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.150				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.164				
I _D (A)	2.3				
Configuration	Single				

SOT-23 (TO-236)

FEATURES

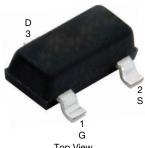
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified ^c
- 100 % R_q and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912

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ROHS COMPLIANT HALOGEN FREE



Marking Code: 8X

2 S	G
	N-Channel MOSFET

ORDERING INFORMATION				
Package	SOT-23			
Lead (Pb)-free and Halogen-free	SQ2308CES-T1-GE3			

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	- I _D	2.3	
	T _C = 125 °C		1.3	
Continuous Source Current (Diode Conduction)		I _S	2.4	Α
Pulsed Drain Current a		I _{DM}	9	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	7	
Single Pulse Avalanche Energy	L=0.11IIII	E _{AS}	2.5	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	D	2	W
	T _C = 125 °C	P_D	0.6	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount b	R_{thJA}	120	°C/W		
Junction-to-Foot (Drain)	-Foot (Drain)		80	C/VV		

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							1	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	\ ,,	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150		
On-State Drain Current a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	Α	
		V _{GS} = 10 V	I _D = 2.3 A	-	0.125	0.150	- Ω	
		V _{GS} = 10 V	I _D = 2.3 A, T _J = 125 °C	1	-	0.250		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 2.3 A, T _J = 175 °C	-	-	0.325		
		V _{GS} = 4.5 V	I _D = 2.1 A	-	0.136	0.164		
Forward Transconductance b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 2.3 A		5.5	-	S	
Dynamic ^b					l	l	•	
Input Capacitance	C _{iss}		V _{DS} = 30 V, f = 1 MHz	-	164	205	pF	
Output Capacitance	Coss	$V_{GS} = 0 V$		-	22	28		
Reverse Transfer Capacitance	C _{rss}			-	14	18		
Total Gate Charge c	Qg			-	3.5	5.3		
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_D = 2 \text{ A}$	-	0.6	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	0.7	-		
Gate Resistance	R _g	f = 1 MHz		2.9	5.84	9	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	4	6		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_L = 15 \Omega$ $I_D \cong 2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	9	13	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	12	17		
Fall Time ^c	t _f			-	12	18		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current a	I _{SM}			-	-	9	А	
	-1	I _F = 1.6 A, V _{GS} = 0					 	

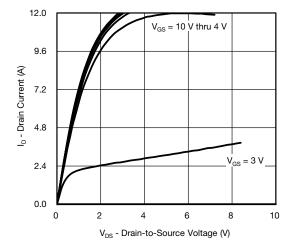
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

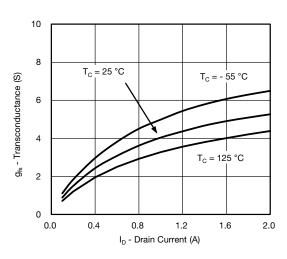
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



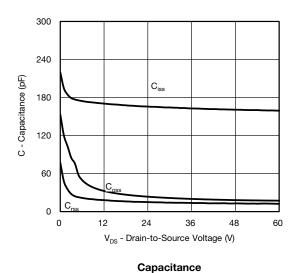
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



Output Characteristics



Transconductance

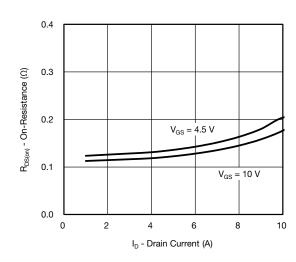


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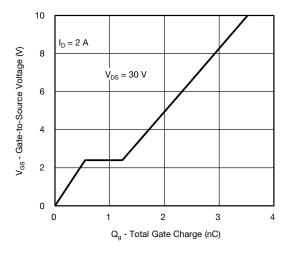
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(4) $T_{C} = 25 \, ^{\circ}C$ 10 $T_{C} = 125 \, ^{\circ}C$ 10 $T_{C} = -55 \, ^{\circ}C$

Transfer Characteristics

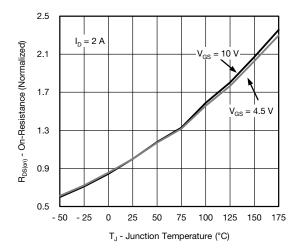


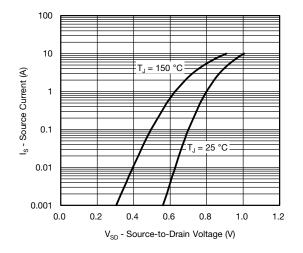
On-Resistance vs. Drain Current





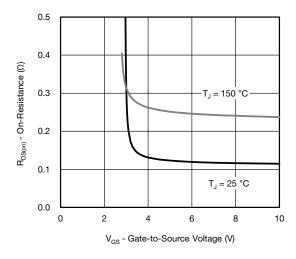
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

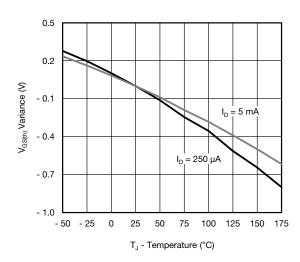




On-Resistance vs. Junction Temperature

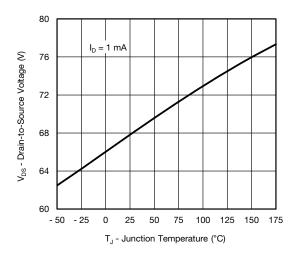






On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

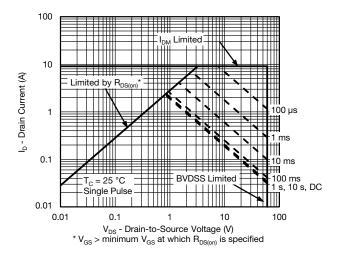


Drain Source Breakdown vs. Junction Temperature

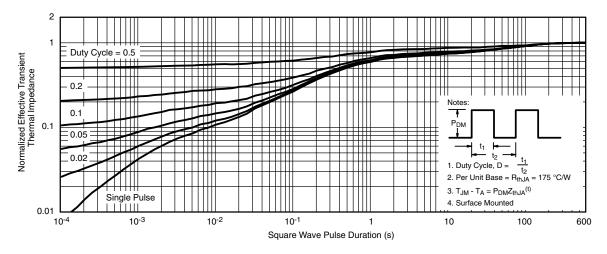
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



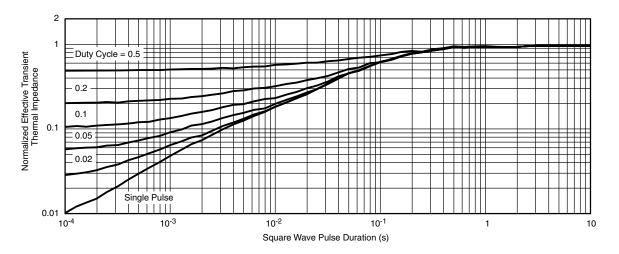
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63877.

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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